

CS-02-015

April 30, 2004



To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/776,794 02/11/04 |

Chyiu-Hyia Poon et al.

MULTIPLE PULSE LASER ANNEALING TO
ACTIVATE ULTRA-SHALLOW JUNCTIONS
| _____ |

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.


The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on May 4, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 5/4/04

U.S. Patent 5,966,605 to Ishida, "Reduction of Poly Depletion in Semiconductor Integrated Circuits," discloses a method for infusing dopant into a polysilicon gate structure by first blanket depositing a dopant enriched layer over the wafer after the polysilicon gate structure has been formed.

U.S. Patent 6,372,585 to Yu, "Semiconductor Device Method," discloses that nitrogen, implanted into silicon can be induced to bond within the silicon by pulsed laser annealing.

U.S. Patent 6,319,761 to Zhang et al., "Method of Fabricating a Thin Film Transistor," discloses that annealing of ion implanted source/drain regions with an excimer laser improves crystallinity and repairs implant damage.

U.S. Patent 6,365,446 to Chong et al., "Formation of Silicided Ultra-Shallow Junctions Using Implant Through Metal Technology and Laser Annealing Process," discloses a method for producing MOS type transistors with deep source/drain junctions and thin, silicided contacts with desirable interfacial and electrical properties.

U.S. Patent 6,391,731 to Chong et al., "Activating Source and Drain Junctions and Extensions Using a Single Laser Anneal," discloses amorphizing both the deep source/drain regions and the shallow source/drain single laser anneal then melting these regions and causing the dopant to distribute.

Sincerely,

A handwritten signature in black ink, appearing to read "Stephen B. Ackerman", with a stylized flourish at the end.

Stephen B. Ackerman,
Reg. No. 37761

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION
MAY 06 2004
(Use several sheets if necessary)

Docket Number (Optional)

CS-02-015

Application Number

10/776,794

Applicant

Poon et al.

Filing Date

02/11/04

Drawn At Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	TITLE	CLASS	SUBCLASS	PLUNG DATE IF APPROPRIATE
	5966605	10/12/99	Ishida	438	299	11/7/97
	6372585	4/16/02	Yu	438	301	9/24/99
	6319761	11/20/01	Zhang et al.	438	166	7/21/97
	6365446	4/2/02	Chong et al.	438	197	7/3/00
	6391731	5/21/02	Chong et al.	438	303	2/15/01

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER

DATE COMPLETED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.